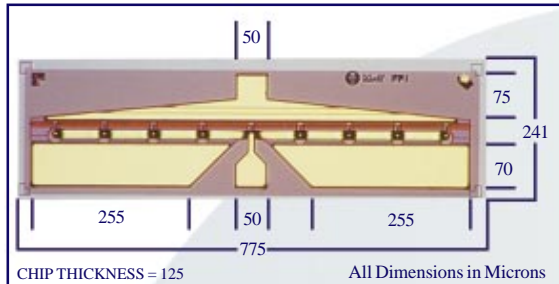


# MwT-1

## 12 GHz High Gain GaAs FET



DOWNLOAD ADDITIONAL DATA [WWW.MWTINC.COM](http://WWW.MWTINC.COM)



### FEATURES

- 10 dB GAIN AT 12 GHz
- EXCELLENT FOR FEEDBACK AMPLIFIER APPLICATIONS 100 MHz TO 12 GHz
- 0.3 MICRON REFRACTORY METAL/GOLD GATE
- 630 MICRON GATE WIDTH
- CHOICE OF CHIP AND THREE PACKAGE TYPES

### DESCRIPTION

The MwT-1 is a GaAs MESFET device whose nominal quarter-micron gate length and 630 micron gate width make it ideally suited to applications requiring high-gain in the 100 MHz to 12 GHz frequency range. The straight geometry of the MwT-1 makes it equally effective for either wideband (e.g. 2 to 6 GHz) or narrow-band applications. The chip is produced using MwT's reliable metal system and devices from each wafer are screened to insure reliability. All chips are passivated using MwT's patented "Diamond-Like Carbon" process for increased durability. Designers can use MwT's unique BIN selection feature to choose devices from narrow Idss ranges, insuring consistent circuit operation.

### DC SPECIFICATIONS AT Ta = 25°C

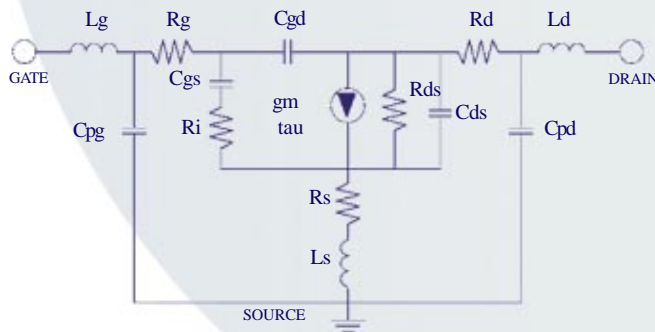
SYMBOL	PARAM. & CONDITIONS	UNITS	MIN	TYP	MAX
<b>IDSS</b>	Saturated Drain Current Vds= 4.0 V VGS= 0.0 V	mA	60		240
<b>Gm</b>	Transconductance Vds= 4.0 V VGS= 0.0 V	mS	90	120	
<b>Vp</b>	Pinch-off Voltage Vds= 3.0 V IDS= 4.0 mA	V		-2.0	-5.0
<b>BVGSO</b>	Gate-to-Source Breakdown Volt. Igs= -1.0 mA	V	-5.0	-10.0	
<b>BVGDO</b>	Gate-to-Drain Breakdown Volt. Igd= -1.0 mA	V	-6.0	-10.0	
<b>Rth</b>	Thermal Resistance MwT-1 Chip, 171 MwT-170, 173	°C/W		80	180*

\*Overall Rth depends on case mounting.

### RF SPECIFICATIONS AT Ta = 25°C

SYMBOL	PARAMETERS AND CONDITIONS	FREQ	UNITS	MIN	TYP
<b>P1dB</b>	Output Power at 1 dB Compression VDS= 5.0 V IDS= 0.6 x IDSS	12 GHz	dBm	23.0	24.0
<b>SSG</b>	Small Signal Gain VDS= 5.0 V IDS= 0.6 x IDSS	12 GHz	dB	9.0	10.0
<b>NFOpt</b>	Optimum Noise Figure VDS= 3.0 V IDS= 30 mA	12 GHz	dB		2.0
<b>GA</b>	Gain@Opt. NF VDS= 3.0V IDS= 30 mA	12 GHz	dB		7.0
<b>IDSS</b>	Recommended IDSS Range for Optimum P1dB		mA		120-210

### DEVICE EQUIVALENT CIRCUIT MODEL



### PARAMETER

### VALUE

Source Resistance	Rs	1.88	Ω
Source Inductance	Ls	0.04	nH
Drain-Source Resistance	Rds	90	Ω
Drain-Source Capacitance	Cds	0.001	pF
Drain Resistance	Rd	2.9	Ω
Drain Pad Capacitance	Cpd	0.145	pF
Drain Inductance	Ld	0.32	nH
Gate Bond Wire Inductance	Lg	0.2	nH
Gate Pad Capacitance	Cpg	0.09	pF
Gate Resistance	Rg	0.83	Ω
Gate-Source Capacitance	Cgs	0.64	pF
Channel Resistance	Ri	4.11	Ω
Gate-Drain Capacitance	Cgd	0.06	pF
Transconductance	gm	130.0	mS
Transit Time	tau	2.0	psec

### ORDERING INFORMATION

Chip	MwT-1
Package 70	MwT-170
Package 71	MwT-171
Package 73	MwT-173

### NOTE:

For Package information, please see supplementary application note from our website at [www.mwtinc.com](http://www.mwtinc.com). When placing order or inquiring, please specify BIN range, wafer no., if known, and screening level required.

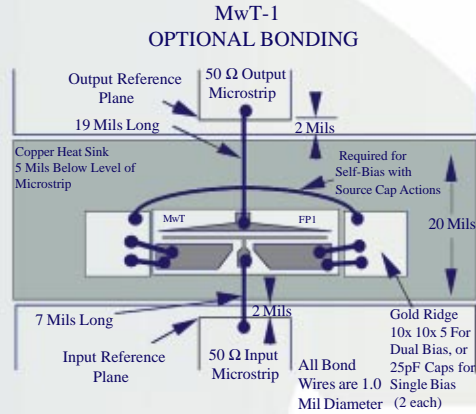
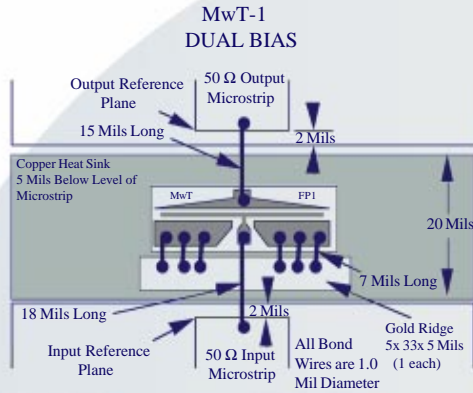
4268 Solar Way Fremont California 94538 Phone: (510) 651-6700 Fax: (510) 651-2208

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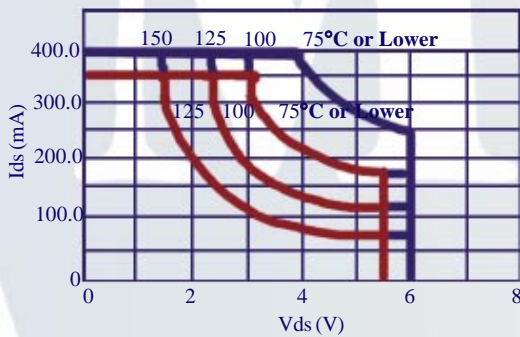
# MwT-1

## 12 GHz High Gain

### GaAs FET



SAFE OPERATING LIMITS vs. BACKSIDE CHIP



### MAXIMUM RATINGS AT Ta = 25°C

SYMBOL	PARAMETER	UNITS	CONT MAX <sup>1</sup>	ABSOLUTE MAX <sup>2</sup>
VDS	Drain to Source Voltage	V	See Safe Operating Limits	
Tch	Channel Temperature	°C	+150	+175
Tst	Storage Temperature	°C	-65 to +150	+175
Pin	RF Input Power	mW	200	300

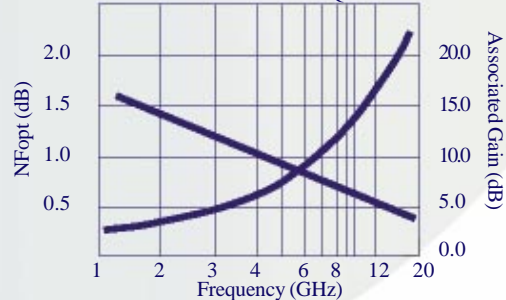
NOTES: 1. Exceeding any one of these limits in continuous operation may reduce the mean-time-to-failure below the design goals.  
2. Exceeding any one of these limits may cause permanent damage.

### TYPICAL NOISE PARAMETERS

MwT-1LN Chip: VDS= 3.0V IDS= 30mA

FREQUENCY GHz	NF MIN dB	GAMMA OPT		Rn/50
		MAG	ANGLE	
1.00	0.45	0.885	32	1.27
2.00	0.65	0.722	61	0.5
4.00	0.95	0.591	110	0.24
6.00	1.25	0.61	139	0.17
8.00	1.52	0.656	157	0.14
12.00	1.88	0.733	176	0.11

### NOISE FIGURE AND ASSOCIATED GAIN VS. FREQUENCY



### BIN SELECTION

BIN#	1	2	3	4	5	6	7	8	9	10	11	12	13	14	15	16	17	18
IDSS (mA)	60-70	70-80	80-90	90-100	100-110	110-120	120-130	130-140	140-150	150-160	160-170	170-180	180-190	190-200	200-210	210-220	220-230	230-240

### BIN ACCURACY STATEMENT

When placing order or inquiring, please specify BIN range, wafer no., if known, and screening level required.